

# LNJ115W85RA1

## Hight Bright Surface Mounting Chip LED

TSS-2 Type

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

#### • Blue

Parameter	Symbol	Rating	Unit
Power dissipation	$P_D$	65	mW
Forward current	$I_F$	15	mA
Pulse forward current *	$I_{FP}$	55	mA
Reverse voltage	$V_R$	5	V
Operating ambient temperature	$T_{opr}$	-30 to +85	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-40 to +100	$^\circ\text{C}$

Note) \*: The condition of  $I_{FP}$  is duty 10%, Pulse width 1 msec.

### ■ Lighting Color

#### • Blue

#### • Red

#### • Red

Parameter	Symbol	Rating	Unit
Power dissipation	$P_D$	55	mW
Forward current	$I_F$	20	mA
Pulse forward current *	$I_{FP}$	60	mA
Reverse voltage	$V_R$	4	V
Operating ambient temperature	$T_{opr}$	-30 to +85	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-40 to +100	$^\circ\text{C}$

Note) \*: The condition of  $I_{FP}$  is duty 10%, Pulse width 1 msec.

### ■ Electro-Optical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

#### • Blue

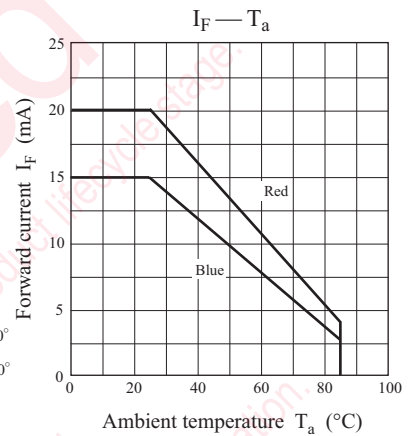
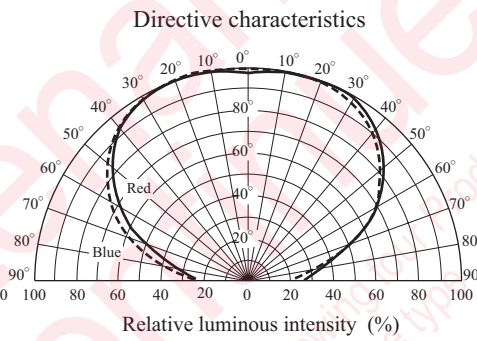
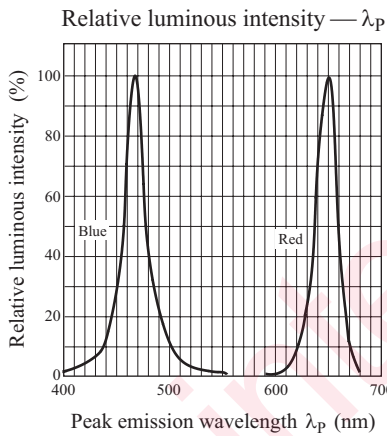
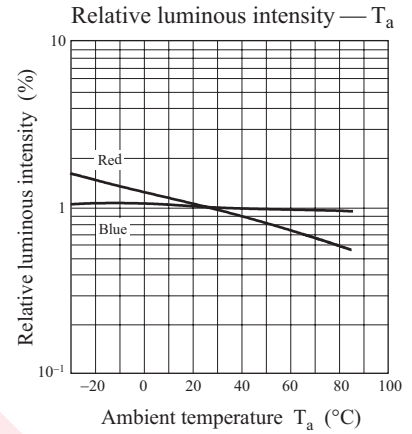
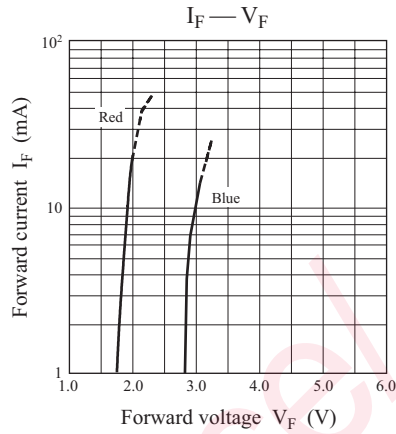
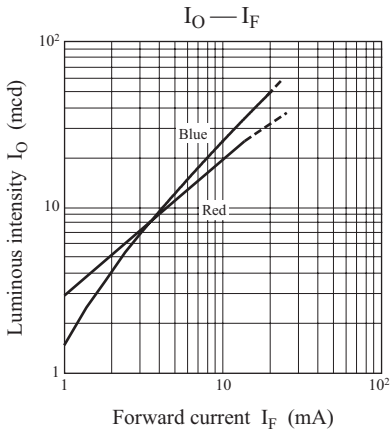
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Luminous intensity *	$I_O$	$I_F = 5 \text{ mA}$	5.0	12.0	41.8	mcd
Reverse current	$I_R$	$V_R = 5 \text{ V}$			100	$\mu\text{A}$
Forward voltage	$V_F$	$I_F = 5 \text{ mA}$		2.90	3.20	V
Peak emission wavelength	$\lambda_p$	$I_F = 5 \text{ mA}$		465		nm
Dominant emission wavelength	$\lambda_d$	$I_F = 5 \text{ mA}$	462	470	478	nm
Spectral half band width	$\Delta\lambda$	$I_F = 5 \text{ mA}$		20		nm

Note) \*: Measurement tolerance:  $\pm 20\%$ 

#### • Red

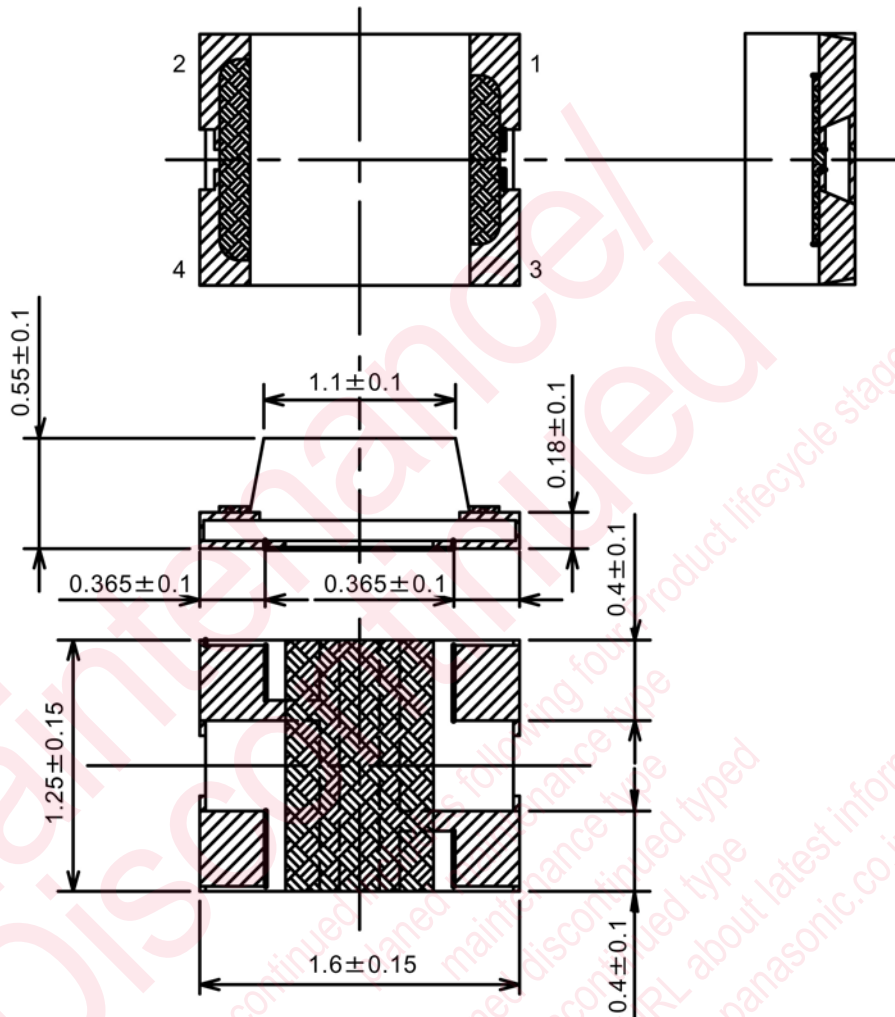
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Luminous intensity *	$I_O$	$I_F = 10 \text{ mA}$	12.0	24.0	60.8	mcd
Reverse current	$I_R$	$V_R = 4 \text{ V}$			100	$\mu\text{A}$
Forward voltage	$V_F$	$I_F = 10 \text{ mA}$		1.92	2.50	V
Peak emission wavelength	$\lambda_p$	$I_F = 10 \text{ mA}$		645		nm
Dominant emission wavelength	$\lambda_d$	$I_F = 10 \text{ mA}$	620	630	640	nm
Spectral half band width	$\Delta\lambda$	$I_F = 10 \text{ mA}$		22		nm

Note) \*: Measurement tolerance:  $\pm 20\%$



■ Package (Unit: mm)

KLTFTN4K1540



- Pin name  
 1, 3: Anode  
 2, 4: Cathode

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